

PJM10H01PSA

Rev-1.1

SuperMOS – SOT-23 -100V BV_{DSS} , 580m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The PJM10H01PSA is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product PJM10H01PSA is Pb-free.

2. Features

- -100V, $R_{DS(ON)}=580m\Omega(TYP.) @V_{GS}=-10V$
 $R_{DS(ON)}=615m\Omega(TYP.) @V_{GS}=-4.5V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

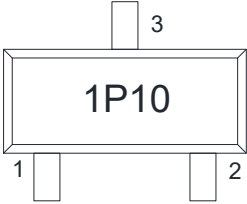
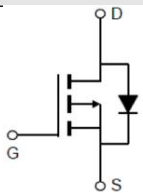
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
PJM10H01PSA	SOT-23	1P10	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

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6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	-0.5	A
	$T_A=100^{\circ}\text{C}$		-0.3	
Maximum Power Dissipation		P_D	0.4	W
Pulsed Drain Current		I_{DM}	-2.3	A
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		280	°C/W

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Electrical Characteristics

At TA = 25°C unless otherwise specified

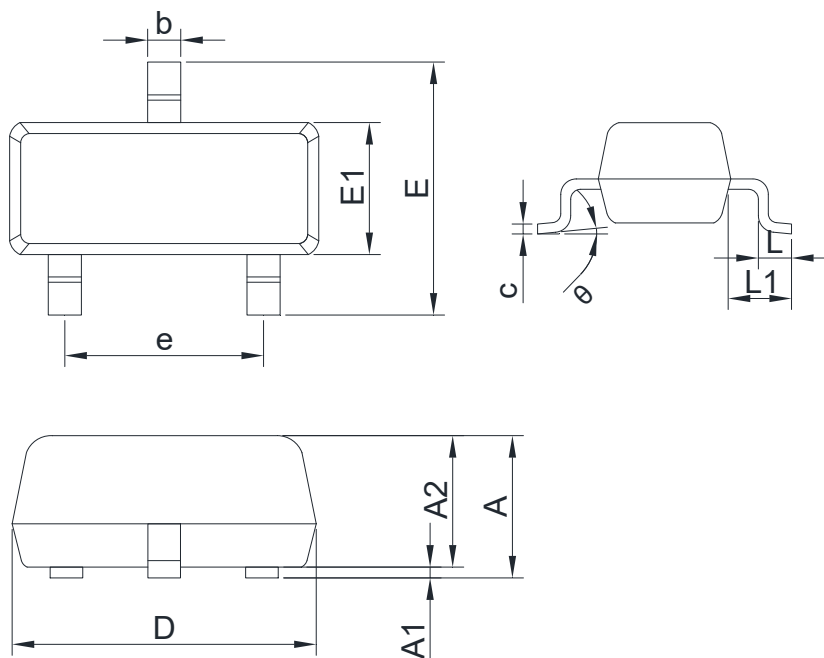
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-100	nA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.1	-1.5	-2.2	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-0.5A		580	788	mΩ
		V _{GS} =-4.5A, I _D =-0.3A		615	858	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-50V f=1MHz		600		pF
Output Capacitance	C _{OSS}			14		
Reverse Transfer Capacitance	C _{RSS}			10		
Total Gate Charge	Q _G	V _{GS} =-10V, V _{DS} =-50V I _D =-0.5A		19.6		nC
Gate-to-Source Charge	Q _{GS}			6		
Gate-to-Drain Charge	Q _{GD}			4.2		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-10V, V _{DS} =-50V I _D =-0.5A, R _G =3Ω		13.5		ns
Rise Time	t _r			3.8		
Turn-Off Delay Time	t _{d(OFF)}			42		
Fall Time	t _f			6.4		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-0.5A	-0.45		-1.2	V

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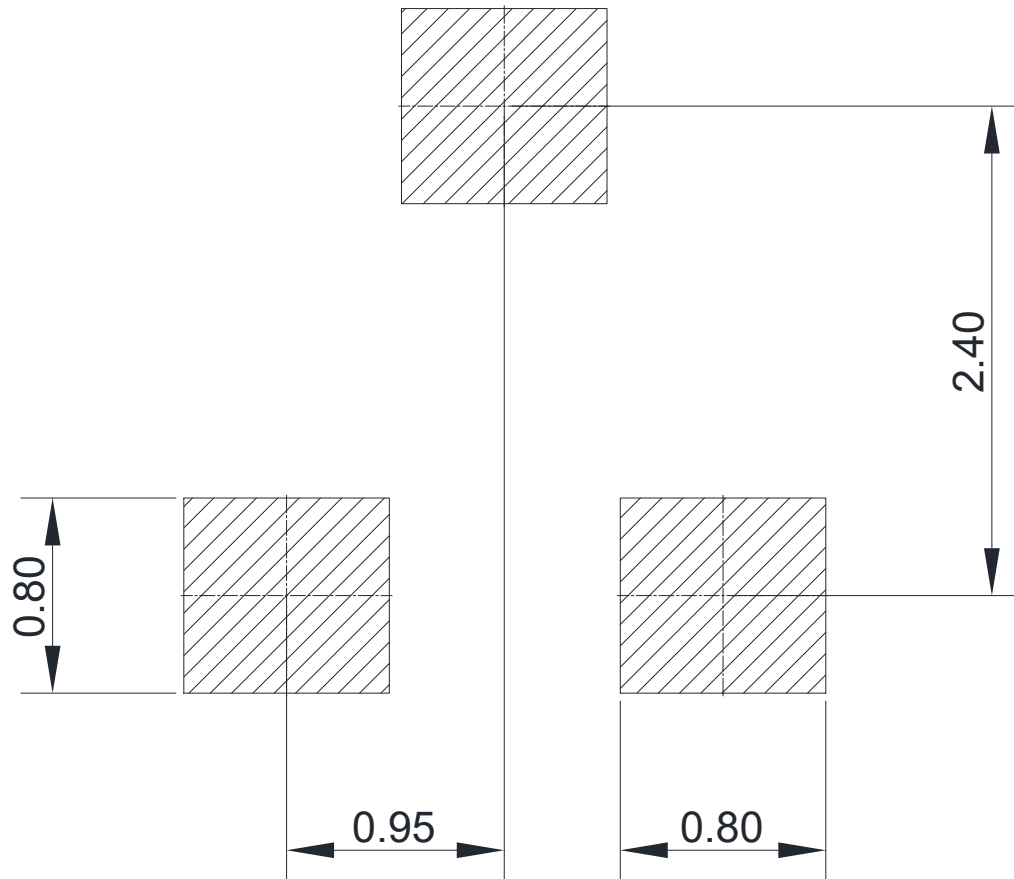
7. Dimension (SOT-23)

POD(Z)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	0.90	1.20	E	2.25	2.55
A1	0.00	0.10	E1	1.20	1.40
A2	0.90	1.10	e	1.80	2.00
b	0.30	0.50	L	0.30	0.50
c	0.07	0.18	L1	0.475	0.625
D	2.80	3.04	θ	0°	8°

8. Recommended Soldering Footprint



DIMENSIONS: MILLIMETERS

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